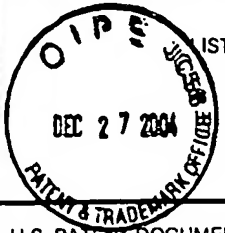




Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2426	SERIAL NO. 10/690,029		
 <p>LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)</p>				APPLICANT: Garo J. Derderian et al.			
				FILING DATE October 20, 2003	GROUP 2812		
U.S. PATENT DOCUMENTS							
Examiner's Initials	Class	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
hw	AA	6,753,618	06/2004	Basceri et al.	257	915	
	AB	5,470,794	11/1995	Anjum	437	200	
	AC	2003/0219942 A1	11/2003	Choi et al.	438	253	
	AD	2004/0245560 A1	12/2004	Pontoh et al.	257	309	
	AE	2004/0245559 A1	12/2004	Pontoh et al.	257	306	
	AF	2004/0046197 A1	03/2004	Basceri et al.	257	296	
	AG	2004/0043228 A1	03/2004	Derderian et al.	428	446	
	AH	2003/0213987 A1	11/2003	Basceri et al.	257	296	
hw	AI	2003/0205729 A1	11/2003	Basceri et al.	257	200	
FOREIGN PATENT DOCUMENTS							
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 OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT: Garo J. Derderian et al.			
				FILING DATE October 20, 2003		GROUP 2812	
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*Examiner's Initials	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
ba	AA 10/932,218		Basceri et al.	1	1	09/01/04	
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hu	AA	3,349,474	12/1963	D. H. Rauscher			
	AB	5,904,517	05/1999	Gardner et al.	438	197	
	AC	5,998,264	12/1999	Wu	438	260	
	AD	6,180,465 B1	01/2001	Gardner et al.	438	291	
	AE	6,207,485 B1	03/2001	Gardner et al.	438	216	
hu	AF	6,548,854 B1	04/2003	Kizilyalli et al.	257	310	
	AG						
hu	AH	2003/0045060 A1	03/2003	Ahn et al.	438	287	
hu	AI	2003/0045078 A1	03/2003	Ahn et al.	438	585	

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hu	AJ	EP 0 851 473 A2	01/1998	EPO			X
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hu	AM	Chang et al., Silicon surface treatments in advanced MOS gate processing, Microelectronic Engineering, (2004), pages 130-135
hu	AN	Lemberger et al., Electrical characterization and reliability aspects of zirconium silicate films obtained from novel MOCVD precursors, Microelectronic Engineering (2004), pages 315-320
hu	AO	Lu et al., Effects of the TaN, interface layer on doped tantalum oxide high-k films, VACUUM (2004), pages 1-9.

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m	AM	Robertson et al., Atomic structure, band offsets, growth and defects at high-K oxide/Si interfaces, Microelectronic Engineering (2004) pages 112-120						
m	AN	Singh et al., High and Low Dielectric Constant Materials, The Electrochemical Society <i>Interface</i> , Summer 1999, pages 26-30						
	AO							
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Glen Hwang		3/05						
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FILING DATE
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2812

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h	AA	4,086,074	04/78	Minot et al.			
	AB	4,622,735	11/86	Shibata			
	AC	4,683,645	08/87	Naguib et al.			
	AD	4,693,910	09/87	Nakajima et al.			
	AE	4,766,090	08/88	Coquin et al.			
	AF	5,099,304	03/92	Takemura et al.			
	AG	5,236,865	08/93	Sandhu et al.			
	AH	5,444,024	08/95	Anjum et al.			
h	AI	5,470,784	11/95	Anjum et al.			

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

h	AA		ABSTRACT: Basceri et al., Atomic Layer Deposition for Nanoscale CU Metalization, 10 pages (pre-April 2004).
h	AN		En et al., Plasma immersion ion implantation reactor design considerations for oxide charging, 85 SURFACE AND COATINGS TECHNOLOGY 64-69 (1966).
h	AO		Ku et al., The Application of Ion Beam Mixing, Doped Silicide, and Rapid Thermal Processing of Self-Aligned Silicide Technology, 137 J. Electrochem. Soc. No. 2, pp. 728-740 (February 1990).

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Gina Hwang

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h	AA	5,670,298	09/97	Hur			
	AB	6,037,239	03/00	Jennings			
	AC	6,096,621	08/00	Jennings			
	AD	6,130,140	10/00	Gonzalez			
	AE	6,133,105	10/00	Chen et al.			
	AF	6,133,116	10/00	Kim et al.			
	AG	6,177,235 B1	01/01	Francou et al.			
	AH	6,277,709 B1	08/01	Wang et al.			
h	AI	6,277,728 B1	08/01	Ahn et al.			

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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

h	AM		ABSTRACT: How to Eliminate Voiding in Porous-Low-k Dielectrics and The Mechanism of Void Formation; Lin et al.; 4 pages
h	AN		COB Stack DRAM Cell Technology beyond 100 nm Technology Node; Yongjik Park & Kinam Kim; pp. 349.1 - 349.3;
h	AO		Rubin et al., Shallow-Junction Diode Formation by implantation of Arsenic and Boron Through Titanium-Silicide Films and ..., 17 IEEE Transactions on Electron Devices, No. 1, pp. 183-190 (January 1990).

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Kina Huang

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	AB	6,465,325 B2	10/02	Ridley et al.			
	AC	6,720,638 B2	04/04	Tran			
	AD	6,780,728 B2	08/04	Tran			
	AE	6,156,674	12/00	Li et al.			
	AF	6,281,100 B1	08/01	Yin et al.			
	AG	6,291,363 B1	09/01	Yin et al.			
	AH	6,380,611 B1	04/02	Yin et al.			
h	AI	6,383,723 B1	05/02	Iyer et al.			

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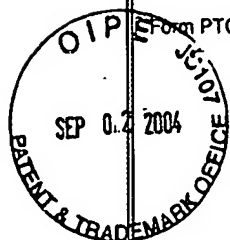
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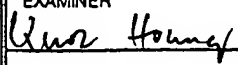
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l	AB	2002/0076879 A1	06/02	Lee et al.	1	1		
l	AC	2002/0196651 A1	12/02	Weis	1	1		
w	AD	2003/0013272 A1	01/03	Hong et al.	1	1		
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l	AC	10/689,958	Basceri			10/03	
l	AD	10/882,118	Sandhu et al.			04/04	
hwy	AE	10/879,367	Blalock et al.			06/04	
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